K. J. SOMAIYA COLLEGE OF ENGINEERING DEPARTMENT OF ELECTRONICS ENGINEERING ELECTRONIC CIRCUITS Single Stage FET Amplifier

Numerical 1:

For the circuit shown in figure 1, Determine I_{D_Q} , V_{GS_Q} , V_{DS} and A_V , if R_S is unbypassed. Given: $I_{DSS} = 12mA$, $V_P = -3V$

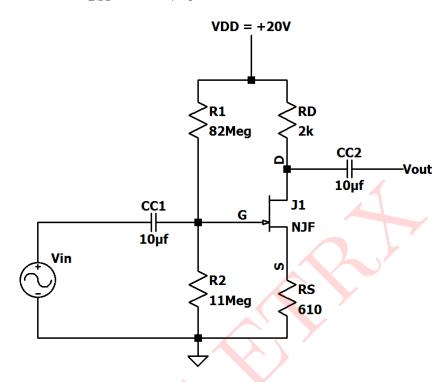


Figure 1: Circuit 1

Solution:

DC Analysis:-

$$V_G = V_{th} = \frac{R_2}{R_1 + R_2} \times V_{DD} = \frac{11M\Omega}{11M\Omega + 82M\Omega} \times 20 = 2.36V$$

 $V_{th}=2.36V$

$$R_{th} = R1 ||R2 = \frac{11M\Omega \times 82M\Omega}{93M\Omega} = 9.698M\Omega$$

$$R_{th}=9.698M\Omega$$

Applying KVL to the Gate-Source loop:-

$$V_{th} - V_{GS} - I_D R_S = 0$$

$$V_{GS} = 2.36 - I_D(610\Omega) \tag{1}$$

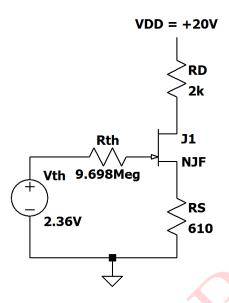


Figure 2: DC Equivalent circuit

For JFET, we assume it in saturation region

$$I_D = I_{DSS} \times \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

$$I_D = 12 \times 10^{-3} \times \left(1 + \frac{V_{GS}}{3}\right)^2 \qquad(2)$$
Put (2) in (1), we get
$$V_{GS} = 2.36 - \left(12mA\left(1 + \frac{V_{GS}}{3}\right)^2 \times 610\right)$$

$$V_{GS} = 2.36 - 7.32 \times \left(1 + \frac{V_{GS}^2}{9} + \frac{2V_{GS}}{3}\right)$$

$$V_{GS} = 2.36 - 7.32 - 0.813V_{GS}^2 - 4.88V_{GS}$$

 $0.813V_{GS}^2 + 5.88V_{GS} + 4.96 = 0$

Solving the above quadratic equation we get,

$$V_{GS} = -0.975V$$
 or $V_{GS} = -6.257V$, We reject this value, as $(V_{GS} > V_P)$ $\therefore V_{GS} = -0.975V$

$$I_D = \frac{2.36 - V_{GS}}{610\Omega} = 5.47 mA \qquad \text{[Using equation 1]}$$

$$I_D = \mathbf{5.47} mA$$

Applying KVL to the drain-source loop,

$$V_{DS} = V_{DD} - I_D \times (R_D + R_S)$$
$$= 20 - 5.47 \times 10^{-3} (2000 + 610) = 5.723$$

$$V_{DS}=5.723$$

Small-Signal parameters:-

$$\begin{split} g_m &= \frac{2I_{DSS}}{|V_P|} \left(1 - \frac{V_{GS}}{V_P}\right) = \frac{2 \times 12mA}{3} \left(1 - \frac{0.975}{3}\right) = 5.4 \frac{mA}{V} \\ \boldsymbol{g_m} &= \mathbf{5.4} \frac{mA}{V} \end{split}$$

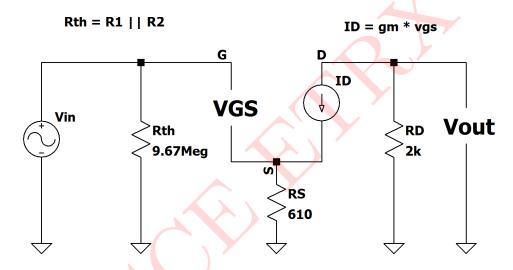


Figure 3: Small Signal Equivalent Circuit

Applying KCL at the collector terminal:-

$$g_m V_{GS} + \frac{V_{out}}{R_D} = 0$$

$$V_{GS} = -\frac{V_{out}}{g_m R_D}$$
.....(3)

Applying KVL to the Gate-Source loop:-

$$V_{in} = V_{GS} + \left(\frac{V_{out}}{R_D}\right) R_S = 0$$

$$V_{in} = -\frac{V_{out}}{g_m R_D} - \frac{V_{out}}{R_D} R_S$$

$$V_{in} = -\frac{V_{out}}{R_D} \left(\frac{1}{g_m} + R_S\right)$$

$$A_V = \frac{V_{out}}{V_{in}} = -\frac{-R_D}{\frac{1}{g_m} + R_S} = \frac{-2k\Omega}{\frac{10^3}{5.4} + 610} = -2.515$$

$$A_V = -2.515$$

SIMULATED RESULTS:

Above circuit was simulated in LTSpice and results are presented below:

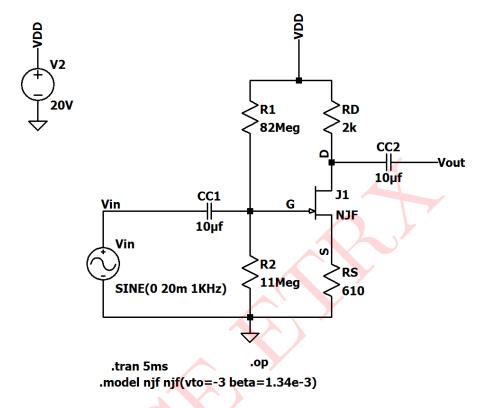


Figure 4: Circuit Schematic 1

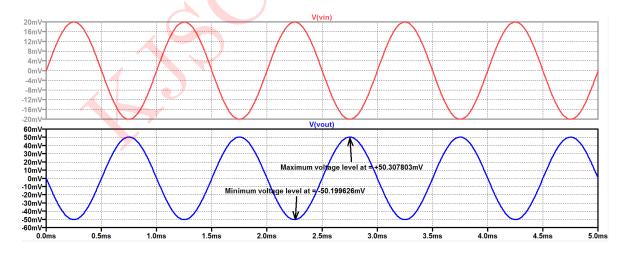


Figure 5: Input & Output waveform

Comparison of Theoretical and Simulated Values:

Parameters	Theoretical	Simulated
I_D	5.47mA	5.48mA
V_{GS}	-0.975V	-0.977V
V_{DS}	5.72V	5.69V
A_V	-2.515	-2.512

Table 1: Numerical 1



Numerical 2:

For the circuit shown in figure 6, $R_L = 10k\Omega$, $V_m = -150V$, $V_t = 2.4V$, $k_n = 2.042 \frac{mA}{V^2}$. Calculate a) Input Resistance R_{in} b) No load voltage gain A_{V_o} c) Output resistance R_o d) Overall voltage gain A_V

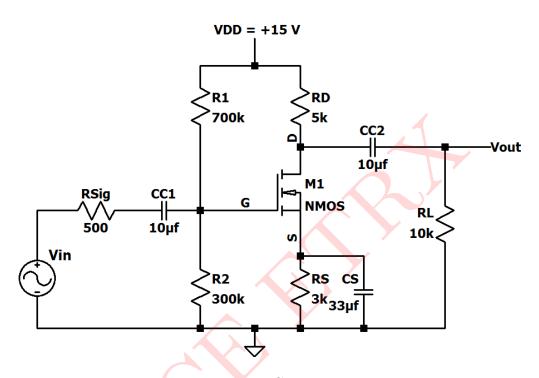


Figure 6: Circuit 2

Solution:

Above circuit 2 is a voltage divider bias employing NMOS:-

DC Analysis:-

$$V_G = V_{th} = \frac{R_2}{R_1 + R_2} \times V_{DD} = \frac{300k\Omega}{700k\Omega + 300k\Omega} \times 15 = 4.5V$$

 $V_{th} = 4.5V$

$$R_{th} = R1||R2 = \frac{700k\Omega \times 300k\Omega}{1000k\Omega} = 210k\Omega$$

$$R_{th}=210k\Omega$$

Applying KVL to the Gate-Source loop:-

$$V_{th} - V_{GS} - I_G R_G - I_D R_S = 0$$

For MOSFET, $I_G = 0$

$$V_{GS} = V_G - I_D R_S$$

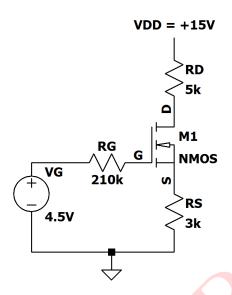


Figure 7: DC Equivalent circuit

For NMOS, we assume it in saturation region

$$I_D = k_n (V_{GS} - V_t)^2 \times (1 + \lambda V_{DS})$$

$$\lambda = \frac{1}{|V_m|} = \frac{1}{150} = 6.67 \times 10^{-3}$$

$$I_D = 2.042 \frac{mA}{V^2} (V_{GS} - 2.4)^2 \times \left(1 + \frac{1}{150} \times V_{DS}\right)$$
......(2)

Applying KVL to the drain-source loop,

$$V_{DS} = V_{DD} - I_D \times (R_D + R_S)$$

$$V_{DS} = 15 - I_D \times (8000\Omega)$$
......(3)
$$I_D = \frac{4.5 - V_{GS}}{3000}$$
 [from equation 1]
......(4)
$$Put (4) \text{ in (3), we get}$$

$$V_{DS} = 15 - \frac{4.5 - V_{GS}}{3000} \times 8000$$

$$V_{DS} = 15 - (12 - 2.67V_{GS})$$

Put (5) and (4) in (2)

$$\frac{4.5 - V_{GS}}{3000} = 2.042 \frac{mA}{V^2} (V_{GS} - 2.4)^2 \times \left(1 + \frac{1}{150} (3 + 2.67 V_{GS})\right)$$
$$\frac{4.5 - V_{GS}}{3000} = 2.042 \frac{mA}{V^2} (V_{GS}^2 + 5.67 - 4.8 V_{GS}) \times (1 + 0.02 + 0.0178 V_{GS})$$

$$4.5 - V_{GS} = 6.126(V_{GS}^2 + 5.76 - 4.8V_{GS})(1.02 + 0.0178V_{GS})$$

$$V_{GS} = 6.25V_{GS}^2 + 36 - 30V_{GS} + 0.11V_{GS}^3 + 0.634V_{GS} - 0.53V_{GS}^2$$

$$0.11V_{GS}^3 + 5.72V_{GS}^2 - 28.37V_{GS} + 31.5 = 0$$

Solving the above cubic equation we get,

$$V_{GS} = -56.64 V$$
, We reject this value, as $(V_{GS} > V_t)$ or $V_{GS} = 2.818 V$

$$\therefore V_{GS} = 2.818V$$

Using equation 4

$$I_D = \frac{4.5 - 2.898}{3000\Omega} = 0.534 mA$$

$$I_D=0.534mA$$

$$V_{DS} = 3 + 2.67V_{GS} = 10.737V$$

$$V_{DS}=10.737V\,$$

Small-Signal parameters:-

$$g_{m} = \frac{dI_{D}}{dV_{DS}} = \frac{d}{dV_{GS}} (k_{n}(V_{GS} - V_{t})^{2} (1 + \lambda V_{DS}))$$

$$g_{m} = 2k_{n}(V_{GS} - V_{t})(1 + \lambda V_{DS}) = 2 \times 2.042 \frac{mA}{V^{2}} \left(2.898 - 2.4 \left(1 + \frac{10.732}{150}\right)\right) = 2.17 \frac{mA}{V}$$

$$g_{m} = 2.17 \frac{mA}{V}$$

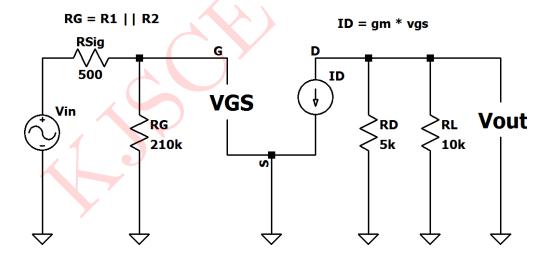


Figure 8: Small Signal Equivalent Circuit

Applying KCL at the drain terminal:-

$$g_m V_{GS} + \frac{V_{out}}{R_D} + \frac{V_{out}}{R_L} = 0$$

$$g_m V_{in} = -V_{out} \left(\frac{1}{R_D} + \frac{1}{R_L} \right)$$

$$\frac{V_{out}}{V_{in}} = -g_m(R_D||R_L)$$

$$A_V = -g_m(R_D||R_L)$$

$$A_V = -2.17 \frac{mA}{V} \left(\frac{5k\Omega \times 10k\Omega}{15k\Omega} \right) = -7.23$$

$$A_V = -7.23$$

$$A_{V_S} = \frac{V_{out}}{V_S} = \frac{V_{out}}{V_{in}} \times \frac{V_{in}}{V_S} = A_V \times \frac{V_{in}}{V_S}$$

$$\frac{V_{in}}{V_S} = \frac{R_1||R_2|}{(R_1||R_2) + R_{sig}} = \frac{210k\Omega}{210k\Omega + 500\Omega} = 0.9976$$

$$A_{V_S} = 0.9976 \times -7.23 = -7.21$$

$$A_{V_S}=-7.21$$

Without Load Resistance(R_L):-

$$A_V = -g_m R_D = -2.17 \times 5k\Omega = 10.85$$

$$A_{V_S} = 0.9976 \times -10.85 = -10.82$$

$$A_{V_S}=-10.82\,$$

Input Impedance:

$$R_i = R_{sig} + (R_1||R_2) = 500 + 210k\Omega = 210.5k\Omega$$

$$R_i=210.5k\Omega$$

Output Impedance:-

$$R_o = R_D || R_L = 5k\Omega || 10k\Omega = 3.34k\Omega$$

$$R_o=3.34k\Omega$$

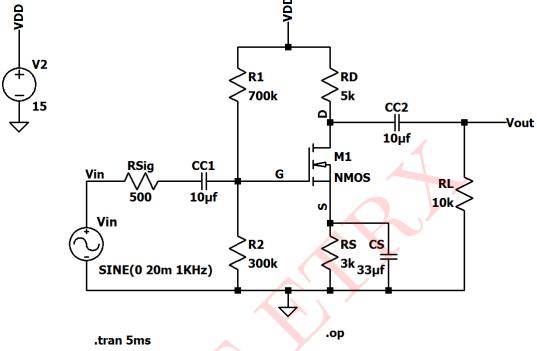
Without Load Resistance(R_L):-

$$R_o = R_D = 5k\Omega$$

$$R_o=5k\Omega$$

SIMULATED RESULTS:

Above circuit was simulated in LTSpice and results are presented below:



.model nmos nmos(vto = 2.4 KP = 4.084e-3 Lambda = 6.67e-3)

Figure 9: Circuit Schematic 2

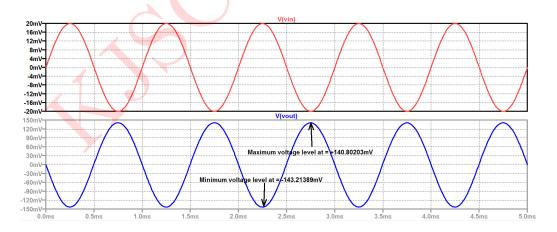


Figure 10: Input & Output waveform

Comparison of Theoretical and Simulated Values:

Parameters	Theoretical	Simulated
I_D	0.534mA	0.535mA
V_{GS}	2.898V	2.894V
A_V	-7.21	-7.10

Table 2: Numerical 2

